



# Bay Linear

## Linear Excellence

### N-Channel Field Effect Transistor

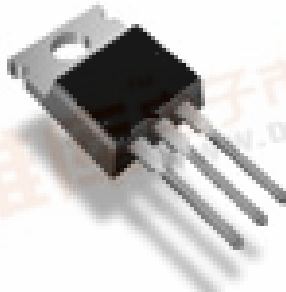
### 60N035

#### Advance Information

#### Description

The Bay Linear n-channel power field effect transistors are produced using high cell density DMOS technology , These devices are particularly suited for low voltage applications such as automotive and other battery powered circuits where fast switching, low in-line power loss and resistance to transistors are needed.

The TO-220 is offered in a 3-pin is universally preferred for all commercial-industrial applications at power dissipation level to approximately to 50 watts. Also, available in a D<sup>2</sup> surface mount power package with a power dissipation up to 2 Watts



#### Features

- **Critical DC Electrical parameters specified at elevated Temp.**
- **Rugged internal source-drain diode can eliminate the need for external Zener diode transient suppresser**
- **Super high density cell design for extremely low R<sub>DS(ON)</sub>**

$$V_{DSS} = 30V$$

$$R_{DS(ON)} = 0.015 \Omega$$

$$I_D = 60A$$

#### Ordering Information

Device	Package	Temp.
60N035T	TO-220	0 to 150°C
60N035S	TO-263 ( D <sup>2</sup> )	0 to 150°C

#### Absolute Maximum Rating

Symbol	Parameter	Max	Unit
I <sub>D</sub>	Drain Current		
	Continues	60	A
	Pulsed	180	
V <sub>DSS</sub>	Drain-Source Voltage	30	V
V <sub>GSV</sub>	Gate Source Voltage	±20	V
P <sub>D</sub>	Total Power Dissipation @ T <sub>C</sub> =25°C	50	W
	Derate above 25°C	0.4	W/°C
T <sub>J</sub>	Operating and Storage	-65 to 175	°C
T <sub>STG</sub>	Temperature Range		



**Electrical Characteristics (  $T_C = 25^\circ\text{C}$  unless otherwise specified)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERSTICS						
B <sub>V</sub> DSS	Drain source breakdown voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =24V V <sub>GS</sub> =0V			10	μA
I <sub>GBLF</sub>	Gate-Body Leakage Forward	V <sub>GS</sub> =20V    V <sub>DS</sub> =0V			100	nA
I <sub>GBLR</sub>	Gate-Body Leakage Reverse	V <sub>GS</sub> =20V    V <sub>DS</sub> =0V			-100	nA
ON CHARACTERSTICS						
V <sub>GS</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =250μA	1		3	V
R <sub>DS(ON)</sub>	Static Drain Voltage	V <sub>GS</sub> =10V, I <sub>D</sub> =26A V <sub>CS</sub> =4.5V, I <sub>O</sub> =21A		0.014	0.015 0.025	Ω
I <sub>D(ON)</sub>	ON-State Drain Current	V <sub>GS</sub> =10V	60			A
g <sub>fs</sub>	Forward Tran conductance					
DYNAMIC CHARACTRISTICS						
C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> = 15V, V <sub>GS</sub> =0V F=1.0 MHZ			1500	pF
C <sub>OSS</sub>	Output Capacitance				700	pF
C <sub>RSS</sub>	Reverse Tras. Capacitance				300	pF
SWITCHING CHARACTERSTICS						
t <sub>D(ON)</sub>	Turn-ON Delay Time	V <sub>DD</sub> =15V I <sub>D</sub> =52A, V <sub>DS</sub> =10V R <sub>GEN</sub> =25Ω			60	nS
t <sub>r</sub>	Turn-ON Rise Time				200	
t <sub>d(off)</sub>	Turn-OFF Delay Time				50	
t <sub>F</sub>	Turn-OFF Fall Time				120	
SOURCE DRAIN DIODE CHRACTERISTICS						
I <sub>S</sub>	Maxim Continuous Drain source Diode Forward Current				60	A
V <sub>DS</sub> (note)	Drain Source Diode Forward Votlage	V <sub>GS</sub> =0V I <sub>S</sub> =26A			1.35	V
THERMAI CHRACTERISTICS						
R <sub>JC</sub>	Thermal Resistance, Junction to Case				2.5	°C/W
R <sub>JC</sub>	Thermal Resistance, Junction to Ambient				62.5	°C/W

Note: Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

**Advance Information-** These data sheets contain descriptions of products that are in development. The specifications are based on the engineering calculations, computer simulations and/ or initial prototype evaluation.

**Preliminary Information-** These data sheets contain minimum and maximum specifications that are based on the initial device characterizations. These limits are subject to change upon the completion of the full characterization over the specified temperature and supply voltage ranges.

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